

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ferroelectric film that is described by a general formula $(\text{Pb}_x\text{A})(\text{B}_{1-x}\text{Nb}_x)\text{O}_3$,

wherein an A element ~~comprises at least one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu~~ consists of an element selected from the group consisting of Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu,

wherein a B element comprises at least one of Zr, Ti, V, W, Hf and Ta, and

wherein x is within the range of: $0.05 \leq x \leq 0.4$.

2. (Currently Amended) A ferroelectric film that is described by $(\text{Pb}_{1-y}\text{A}_y)(\text{B}_{1-x}\text{Nb}_x)\text{O}_3$,

wherein an A element ~~comprises at least one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu~~ consists of an element selected from the group consisting of Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu,

wherein y is within the range of: $0 < y \leq 0.2$,

wherein a B element comprises at least one of Zr, Ti, V, W, Hf and Ta, and

wherein x is within the range of: $0.05 \leq x \leq 0.4$.

3-7. (Canceled)

8. (Currently Amended) The ferroelectric film as defined by claim 1, further comprising:

Si, Ge or Si and Ge.

9. (Currently Amended) The ferroelectric film as defined by claim 1, further comprising:

Si, Ge or Si and Ge of from about 0.5 mol% to about 5 mol%.

10-23. (Canceled)

24. (Previously Presented) A ferroelectric memory device comprising:

a substrate;

a transistor formed on the substrate; and

a ferroelectric capacitor formed above the substrate,

wherein the ferroelectric capacitor comprises a ferroelectric film as defined by

claim 1.

25. (Previously Presented) A piezoelectric actuator comprising:

a substrate; and

a piezoelectric element formed above the substrate,

wherein the piezoelectric element comprises a ferroelectric film as defined by

claim 1.

26. (Canceled)

27. (Currently Amended) The ferroelectric film as defined by claim 2, further

comprising:

Si, Ge or Si and Ge.

28. (Currently Amended) The ferroelectric film as defined by claim 2, further

comprising:

Si, Ge or Si and Ge of from about 0.5 mol% to about 5 mol%.

29. (Previously Presented) A ferroelectric memory device comprising:

a substrate;

a transistor formed on the substrate; and

a ferroelectric capacitor formed above the substrate,

wherein the ferroelectric capacitor comprises a ferroelectric film as defined by

claim 2.

30. (Previously Presented) A piezoelectric actuator comprising:
a substrate; and
a piezoelectric element formed above the substrate,
wherein the piezoelectric element comprises a ferroelectric film as defined by claim 2.

31. (New) The ferroelectric film as defined by claim 1, wherein the B element comprises at least Zr and Ti, and optionally further includes any of V, W, Hf or Ta, and wherein a mol% of Ti is greater than a mol% of Zr.

32. (New) The ferroelectric film as defined by claim 2, wherein the B element comprises at least Zr and Ti, and optionally further includes any of V, W, Hf or Ta, and wherein a mol% of Ti is greater than a mol% of Zr.